Silicon PNP Power Transistors 2SB857 2SB858

DESCRIPTION

・With TO-220C package
・Complement to type 2SD1133/1134

APPLICATIONS

・Low frequency power amplifier

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

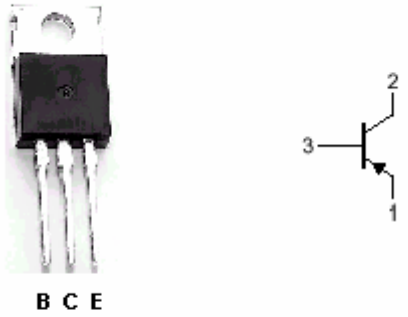

Fig.1 simplified outline (TO-220C) and symbol

Absolute maximum ratings(Tc=25℃)

SYMBOL	PARAMETER		CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage		Open emitter	-70	V
V_{CEO}	Collector-emitter voltage	2SB857	Open base	-50	V
		2SB858		-60	
V_{EBO}	Emitter-base voltage		Open collector	-5	V
I_C	Collector current			-4	A
I_{CP}	Collector current-peak			-8	A
P_C	Collector power dissipation		T_C=25℃	40	W
T_j	Junction temperature			150	℃
T_{stg}	Storage temperature			-45~150	℃

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CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	2SB857	I_C=-50mA; R_{BE}=∞	-50			V
		2SB858		-60			
$V_{(BR)CBO}$	Collector-base breakdown voltage		I_C=-10 μA; I_E=0	-70			V
$V_{(BR)EBO}$	Emitter-base breakdown votage		I_E=-10 μA; I_C=0	-5			V
V_{CEsat}	Collector-emitter saturation voltage		I_C=-2 A;I_B=-0.2 A			-1.0	V
V_{BE}	Base-emitter voltage		I_C=-1A ; V_{CE}=-4V			-1.0	V
I_{CBO}	Collector cut-off current		V_{CB}=-50V; I_E=0			-1	μA
h_{FE-1}	DC current gain		I_C=-1A ; V_{CE}=-4V	60		320	
h_{FE-2}	DC current gain		I_C=-0.1A ; V_{CE}=-4V	35			
f_T	Transition frequency		I_C=-0.5A ; V_{CE}=-4V		15		MHz

◆ **h_{FE-1} classifications**

B	C	D
60-120	100-200	160-320

PACKAGE OUTLINE

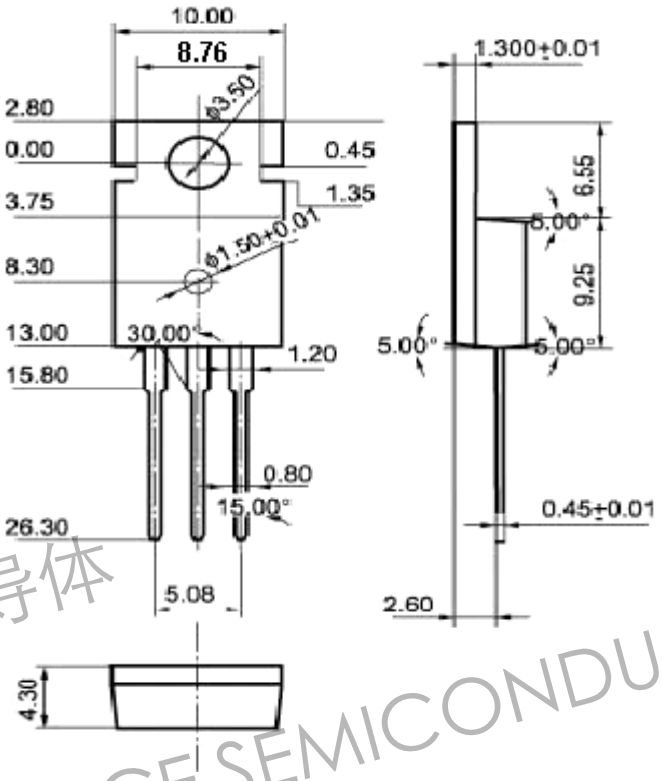

Fig.2 Outline dimensions (unindicated tolerance:±0.10 mm)

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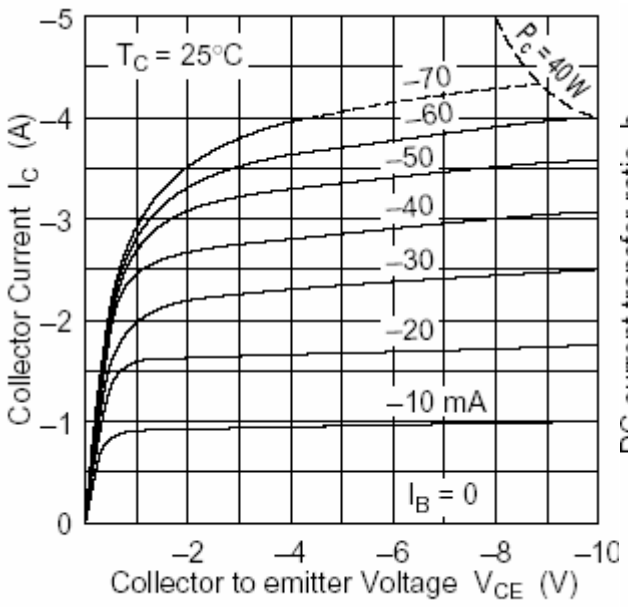

Fig.3 Static Characteristic

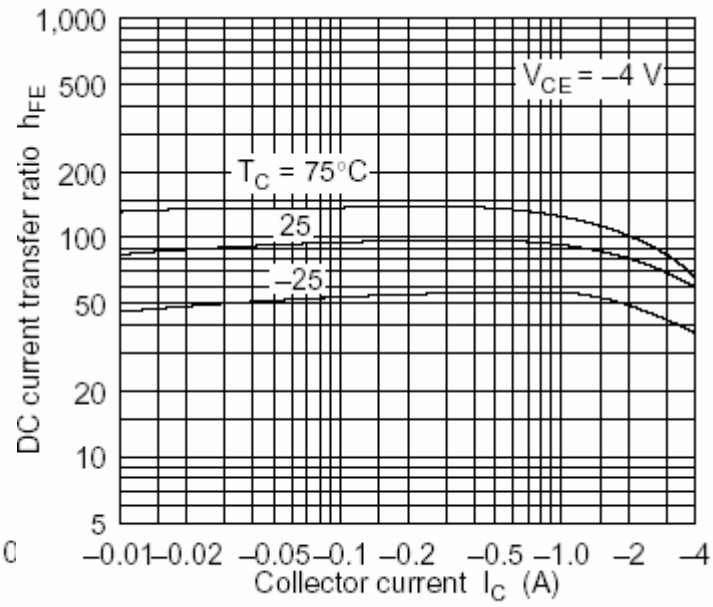

Fig.4 DC current Gain

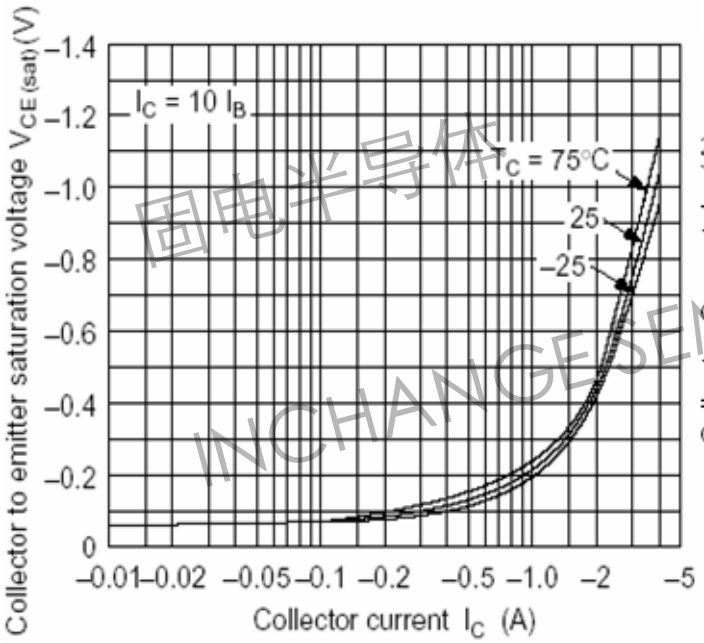

Fig.5 Collector-Emitter Saturation Voltage

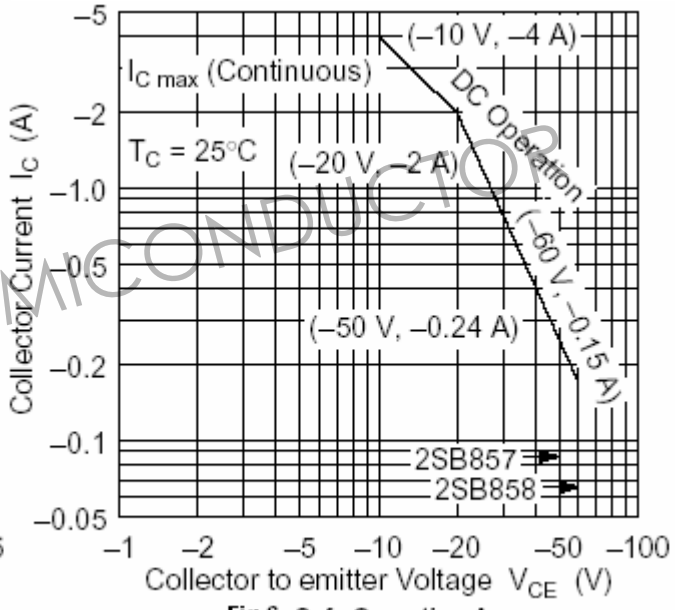

Fig.6 Safe Operating Area